

AUTOSWITCHING POWER MUX

Check for Samples: TPS2110A, TPS2111A

FEATURES

- Two-Input, One-Output Power Multiplexer with Low r_{DS(on)} Switches:
 - 84 mΩ Typ (TPS2111A)
 - 120 mΩ Typ (TPS2110A)
- Reverse and Cross-Conduction Blocking
- Wide Operating Voltage Range: 2.8 V to 5.5 V
- Low Standby Current: 0.5 μA Typ
 Low Operating Current: 55 μA Typ
- Adjustable Current Limit
- Controlled Output Voltage Transition Time: Limits Inrush Current Minimizes Output Voltage Hold-Up Capacitance
- CMOS- and TTL-Compatible Control Inputs
- Manual and Auto-Switching Operating Modes
- Thermal Shutdown
- Available in a TSSOP-8 Package

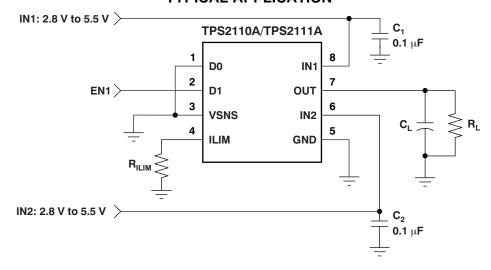
APPLICATIONS

- PCs
- PDAs
- Digital Cameras
- Modems
- Cell Phones
- Digital Radios
- MP3 Players

DESCRIPTION

The TPS211xA family of power multiplexers enables seamless transition between two power supplies, such as a battery and a wall adapter, each operating at 2.8 V to 5.5 V and delivering up to 1 A. The TPS211xA family includes extensive protection circuitry, including user-programmable current limiting, thermal protection, inrush current control, seamless supply transition, cross-conduction blocking, and reverse-conduction blocking. These features greatly simplify designing power multiplexer applications.

TYPICAL APPLICATION



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This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

AVAILABLE OPTIONS

FEATUR	TPS2110A	TPS2111A	TPS2112A	TPS2113A	TPS2114A	TPS2115A	
Current Limit Adjustment F	0.31 A to 0.75 A	0.63 A to 1.25 A	0.31 A to 0.75 A	0.63 A to 1.25 A	0.31 A to 0.75 A	0.63 A to 1.25 A	
Curitahina Madaa	Manual	Yes	Yes	No	No	Yes	Yes
Switching Modes	Automatic	Yes	Yes	Yes	Yes	Yes	Yes
Switch Status Output		No	No	Yes	Yes	Yes	Yes

ORDERING INFORMATION⁽¹⁾

T _A	PACKAGE	ORDERING NUMBER	PACKAGE MARKING
40°C to 05°C	TCCOD Q (DM)	TPS2110APW	2110A
−40°C to 85°C	TSSOP-8 (PW)	TPS2111APW	2111A

⁽¹⁾ For the most current package and ordering information see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.

ABSOLUTE MAXIMUM RATINGS(1)

Over recommended operating junction temperature range, unless otherwise noted.

			TPS2110A, TPS2111A	UNIT		
Input vo	Itage range at pins IN1, II	N2, D0, D1, VSNS, ILIM ⁽²⁾	-0.3 to 6	V		
Output v	voltage range, V _{O(OUT)} (2)		-0.3 to 6	V		
,		TPS2110A	0.9	Α		
Continue	Continuous output current, I _O TPS2111A		1.5			
Continuo	ous total power dissipation	n	See Dissipation Ratings table			
Operatin	ng virtual junction tempera	ature range, T _J	Internally Limite	ed		
Human body model (H		BM)	2	kV		
ESD	Charged device model (CDM)		500	V		

⁽¹⁾ Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

DISSIPATION RATINGS

PACKAGE	DERATING FACTOR	T _A ≤ 25°C POWER	T _A = 70°C POWER	T _A = 85°C POWER
	ABOVE T _A = 25°C	RATING	RATING	RATING
TSSOP-8 (PW)	3.9 mW/°C	387 mW	213 mW	155 mW

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⁽²⁾ All voltages are with respect to GND.



RECOMMENDED OPERATING CONDITIONS

		TPS211	0A, TPS2111A			
		MIN	NOM	MAX	UNIT	
land to the same of INIA V	V _{I(IN2)} ≥ 2.8 V	1.5		5.5	V	
put voltage at IN1, V _{I(IN1)}	V _{I(IN2)} < 2.8 V	2.8		5.5	V	
nput voltage at IN2, V _{I(IN2)}	V _{I(IN1)} ≥ 2.8 V	1.5		5.5	- V	
input voitage at inz, v _{I(IN2)}	$V_{I(IN1)} < 2.8 \text{ V}$	2.8		5.5		
Input voltage: V _{I(DO)} , V _{I(D1)} , V _{I(VSNS)}	•	0		5.5	V	
Current limit adjustment renge	TPS2110A	0.31		0.75		
Current limit adjustment range, I _{O(OUT)}	TPS2111A	0.63		1.25	Α	
Operating virtual junction temperature, T	J	-40		125	°C	

ELECTRICAL CHARACTERISTICS: Power Switch

Over recommended operating junction temperature, $V_{I(IN1)} = V_{I(IN2)} = 5.5 \text{ V}$, and $R_{ILIM} = 400 \Omega$, unless otherwise noted.

			(((()		PS2110A		TF	S2111A		
PARAMETER		TEST	CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
			$V_{I(IN1)} = V_{I(IN2)} = 5.0 \text{ V}$		120	140		84	110	
Drain-source	r _{DS(on)} ⁽¹⁾	$T_{J} = 25^{\circ}\text{C},$ $I_{L} = 500 \text{ mA}$	$V_{I(IN1)} = V_{I(IN2)} = 3.3 \text{ V}$		120	140		84	110	$m\Omega$
on-state			$V_{I(IN1)} = V_{I(IN2)} = 2.8 \text{ V}$		120	140		84	110	
resistance (INx-OUT)				$V_{I(IN1)} = V_{I(IN2)} = 5.0 \text{ V}$			220			150
(114x-001)		$T_J = 125^{\circ}C,$ $I_L = 500 \text{ mA}$	$V_{I(IN1)} = V_{I(IN2)} = 3.3 \text{ V}$			220			150	$m\Omega$
		333 1171	V _{I(IN1)} = V _{I(IN2)} = 2.8 V			220			150	

¹⁾ The TPS211xA can switch a voltage as low as 1.5 V as long as there is a minimum of 2.8 V at one of the input power pins. In this specific case, the lower supply voltage has no effect on the IN1 and IN2 switch on-resistances.

ELECTRICAL CHARACTERISTICS

Over recommended operating junction temperature, $V_{I(IN1)} = V_{I(IN2)} = 5.5 \text{ V}$, $I_{O(OUT)} = 0 \text{ A}$, and $R_{ILIM} = 400 \Omega$, unless otherwise noted.

PARAMETER			TPS2110	0A, TPS211	1A		
		TEST CONDITIONS	MIN	TYP	MAX	UNIT	
LOGIC INPUTS (D0 AND	D1)						
High-level input voltage	V _{IH}		2			V	
Low-level input voltage	V _{IL}				0.7	٧	
lanut sumant at DO as D4	·	D0 or D1 = High, sink current			1	^	
Input current at D0 or D1		D0 or D1 = Low, source current	0.5	1.4	5	μΑ	
SUPPLY AND LEAKAGE	CURRENTS						
		D1 = High, D0 = Low (IN1 active), $V_{I(IN2)} = 3.3 \text{ V}$		55	90		
Supply current from IN1 (o	perating)	D1 = High, D0 = Low (IN1 active), $V_{I(IN1)} = 3.3 \text{ V}$		1	12	μА	
		$D0 = D1 = Low (IN2 active), V_{I(IN2)} = 3.3 V$			75		
		$D0 = D1 = Low (IN2 active), V_{I(IN1)} = 3.3 V$			1		
Supply current from IN2 (operating)		D1 = High, D0 = Low (IN1 active), $V_{I(IN2)} = 3.3 \text{ V}$			1		
		D1 = High, D0 = Low (IN1 active), $V_{I(IN1)} = 3.3 \text{ V}$			75	μΑ	
		D0 = D1 = Low (IN2 active), V _{I(IN2)} = 3.3 V		1	12	<u>.</u>	
		$D0 = D1 = Low (IN2 active), V_{I(IN1)} = 3.3 V$		55	90		



Over recommended operating junction temperature, $V_{I(IN1)} = V_{I(IN2)} = 5.5 \text{ V}$, $I_{O(OUT)} = 0 \text{ A}$, and $R_{ILIM} = 400 \Omega$, unless otherwise noted.

			TPS211	0A, TPS211	1A	-
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
SUPPLY AND LEAKAGE CO	JRRENTS, con	ntinued				
0:	. " `	D0 = D1 = High (inactive), V _{I(IN2)} = 3.3 V		0.5	2	
Quiescent current from IN1 (s	standby)	D0 = D1 = High (inactive), V _{I(IN1)} = 3.3 V			1	μΑ
O	- 1 A	D0 = D1 = High (inactive), V _{I(IN2)} = 3.3 V			1	^
Quiescent current from IN2 (s	standby)	D0 = D1 = High (inactive), V _{I(IN1)} = 3.3 V		0.5	2	μΑ
Forward leakage current from (measured from OUT to GND		D0 = D1 = High (inactive), IN2 open, $V_{O(OUT)}$ = 0 V (shorted), T_J = 25°C		0.1	5	μА
Forward leakage current from (measured from OUT to GND		D0 = D1 = High (inactive), IN1 open, $V_{O(OUT)}$ = 0 V (shorted), T_J = 25°C		0.1	5	μА
Reverse leakage current to Infrom INx to GND)	Nx (measured	D0 = D1 = High (inactive), $V_{I(INx)} = 0 \text{ V}$, $V_{O(OUT)} = 5.5 \text{ V}$, $T_J = 25^{\circ}\text{C}$		0.3	5	μΑ
CURRENT LIMIT CIRCUIT					'	
	TD00//01	$R_{ILIM} = 400 \Omega$	0.51	0.63	0.80	
Ourse at Park	TPS2110A	R _{ILIM} = 700 Ω	0.30	0.36	0.50	Α
Current limit accuracy	TD004444	R _{ILIM} = 400 Ω	0.95	1.25	1.56	
	TPS2111A	$R_{ILIM} = 700 \Omega$	0.47	0.71	0.99	Α
Current limit settling time	t _d	Time for short-circuit output current to settle within 10% of its steady state value.		1		ms
Input current at ILIM		$V_{I(ILIM)} = 0 \text{ V}, I_{O(OUT)} = 0 \text{ A}$	-15		0	μΑ
VSNS COMPARATOR		(12)			l	
VSNS threshold voltage		V _{I(VSNS)} ↑	0.78	0.80	0.82	
		V _I (vsns) ↓	0.735	0.755	0.775	V
VSNS comparator hysteresis		(10.10)			60	mV
Deglitch of VSNS comparator	r (both ↑↓)		90	150	220	μS
Input current		0 V ≤ V _{I(VSNS)} ≤ 5.5 V	-1		1	μΑ
UVLO					1	
INIA I INIG I II / I O		Falling edge	1.15	1.25		.,
IN1 and IN2 UVLO		Rising edge		1.30	1.35	V
IN1 and IN2 UVLO hysteresis	S		30	57	65	mV
Internal V _{DD} UVLO		Falling edge	2.4	2.53		
(the higher of IN1 and IN2)		Rising edge		2.58	2.8	V
Internal V _{DD} UVLO hysteresis	3		30	50	75	mV
UVLO deglitch for IN1, IN2		Falling edge		110		μS
REVERSE CONDUCTION B	LOCKING				'	
Minimum output-to-input voltage difference to block switching	$\Delta V_{O(I_block)}$	D0 = D1 = high, $V_{I(INx)}$ = 3.3 V. Connect OUT to a 5-V supply through a series 1-kΩ resistor. Let D0 = low. Slowly decrease the supply voltage until OUT connects to IN1.	80	100	120	mV
THERMAL SHUTDOWN						
Thermal shutdown threshold		TPS211xA is in current limit.	135			°C
Recovery from thermal shutd	own	TPS211xA is in current limit.	125			°C
Hysteresis				10		°C
IN2-IN1 COMPARATORS						
Hysteresis of IN2-IN1 compa	rator		0.1		0.2	V
Deglitch of IN2-IN1 compara	tor (both ↑ ⊥)		10	20	50	μS

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SWITCHING CHARACTERISTICS

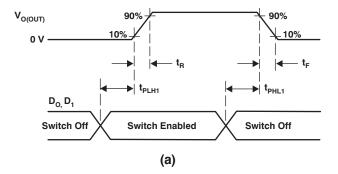
Over recommended operating junction temperature, $V_{I(IN1)} = V_{I(IN2)} = 5.5 \text{ V}$, and $R_{ILIM} = 400 \Omega$, unless otherwise noted.

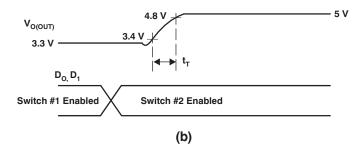
				TF	TPS2110A		TP	S2111A		
P	ARAMETER	TEST CO	NDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
t _R	Output rise time from an enable	$V_{I(IN1)} = V_{I(IN2)} = 5 \text{ V}$	$T_J = 25^{\circ}\text{C},$ $C_L = 1 \mu\text{F},$ $I_L = 500 \text{ mA}; \text{ see}$ Figure 1(a).	0.5	1.0	1.5	1	1.8	3	ms
t _F	Output fall time from a disable	$V_{I(IN1)} = V_{I(IN2)} = 5 \text{ V}$	$T_J = 25^{\circ}\text{C},$ $C_L = 1 \mu\text{F},$ $I_L = 500 \text{ mA}; \text{see}$ Figure 1(a).	0.35	0.5	0.7	0.5	1	2	ms
t _T T		IN1 to IN2 transition, $V_{I(IN1)} = 3.3 \text{ V},$ $V_{I(IN2)} = 5 \text{ V}$	$T_J = 125^{\circ}\text{C},$ $C_L = 10 \mu\text{F},$ $I_L = 500 \text{mA};$ measure transition		40	60		40	60	
	Transition time	IN2 to IN1 transition, $V_{I(IN1)} = 5 \text{ V}$, $V_{I(IN2)} = 3.3 \text{ V}$	time as 10% to 90% rise time or from 3.4 V to 4.8 V on V _{O(OUT)} . See Figure 1(b).		40	60		40	60	μS
t _{PLH1}	Turn-on propagation delay from an enable	$V_{I(IN1)} = VI_{(IN2)} = 5 \text{ V}$ Measured from enable to 10% of $V_{O(OUT)}$	$T_J = 25^{\circ}C$, $C_L = 10 \mu F$, $I_L = 500 \text{ mA}$; see Figure 1(a).		0.5			1		ms
t _{PHL1}	Turn-off propagation delay from a disable	$V_{I(IN1)} = VI_{(IN2)} = 5 V$ Measured from disable to 90% of $V_{O(OUT)}$	$T_J = 25^{\circ}\text{C},$ $C_L = 10 \ \mu\text{F},$ $I_L = 500 \ \text{mA};$ see Figure 1(a).		3			5		ms
t _{PLH2}	Switch-over rising propagation delay	$\begin{aligned} &\text{Logic 1 to Logic 0} \\ &\text{transition on D1,} \\ &V_{I(IN1)} = 1.5 \text{ V,} \\ &V_{I(IN2)} = 5 \text{ V,} \\ &V_{I(OD)} = 0 \text{ V,} \\ &\text{Measured from D1 to} \\ &10\% \text{ of } V_{O(OUT)} \end{aligned}$	$T_J = 25^{\circ}\text{C},$ $C_L = 10 \mu\text{F},$ $I_L = 500 \text{mA}; \text{see}$ Figure 1(c).		40	100		40	100	μs
t _{PHL2}	Switch-over falling propagation delay	$ \begin{array}{l} \text{Logic 0 to Logic 1} \\ \text{transition on D1,} \\ V_{\text{I(IN1)}} = 1.5 \text{ V,} \\ V_{\text{I(IN2)}} = 5 \text{ V,} \\ V_{\text{I(D0)}} = 0 \text{ V,} \\ \text{Measured from D1 to} \\ 90\% \text{ of } V_{\text{O(OUT)}} \\ \end{array} $	$T_J = 25^{\circ}\text{C},$ $C_L = 10 \mu\text{F},$ $I_L = 500 \text{mA}; \text{see}$ Figure 1(c).	2	3	10	2	5	10	ms



PARAMETER MEASUREMENT INFORMATION

TIMING WAVEFORMS





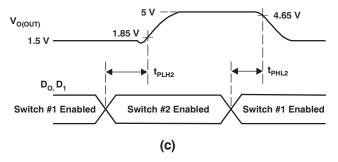


Figure 1. Propagation Delays and Transition Timing Waveforms



DEVICE INFORMATION

TRUTH TABLE

D1	D0	$V_{I(VSNS)} > 0.8 V^{(1)}$	$V_{I(IN2)} > V_{I(IN1)}$	OUT ⁽²⁾
0	0	X	X	IN2
0	1	Yes	X	IN1
0	1	No	No	IN1
0	1	No	Yes	IN2
1	0	X	X	IN1
1	1	X	X	Hi-Z

⁽¹⁾ X = Don't care.

PIN CONFIGURATIONS

PW PACKAGE TSSOP-8 (TOP VIEW)

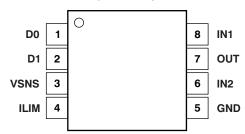


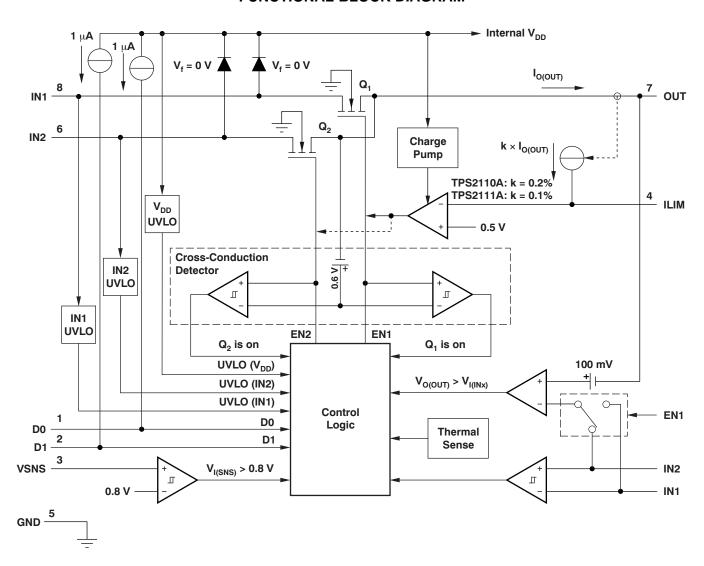
Table 1. TERMINAL FUNCTIONS

TERM	TERMINAL		
NAME	NO.	1/0	DESCRIPTION
D0	1	I	TTL- and CMOS-compatible input pins. Each pin has a 1-μA pull-up. The Truth Table
D1	2	1	illustrates the functionality of D0 and D1.
GND	5	Power	Ground
IN1	8	I	Primary power switch input. The IN1 switch can be enabled only if the IN1 supply is above the UVLO threshold and at least one supply exceeds the internal V_{DD} UVLO.
IN2	6	1	Secondary power switch input. The IN2 switch can be enabled only if the IN2 supply is above the UVLO threshold and at least one supply exceeds the internal V _{DD} UVLO.
ILIM	4	1	A resistor (R_{ILIM}) from ILIM to GND sets the current limit I_L to 250/ R_{ILIM} and 500/ R_{ILIM} for the TPS2110A and TPS2111A, respectively.
OUT	7	0	Power switch output
VSNS	3	I	In the auto-switching mode (D0 = 1, D1 = 0), an internal power FET connects OUT to IN1 if the VSNS voltage is greater than 0.8 V. Otherwise, the FET connects OUT to the higher of IN1 and IN2. The Truth Table illustrates the functionality of VSNS.

⁽²⁾ The undervoltage lockout circuit causes the output to go Hi-Z if the selected power supply does not exceed the IN1/IN2 UVLO, or if neither of the supplies exceeds the internal V_{DD} UVLO.



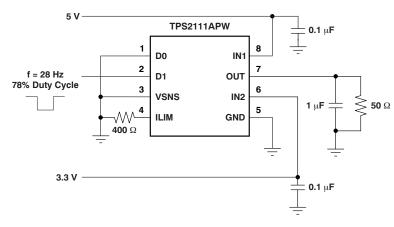
FUNCTIONAL BLOCK DIAGRAM





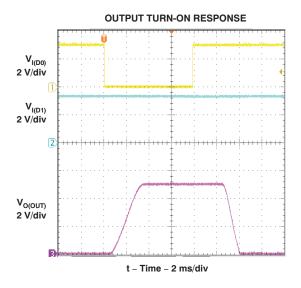
TYPICAL CHARACTERISTICS

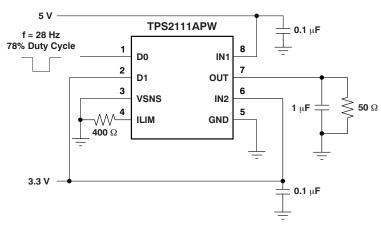
V_{I(D0)} 2 V/div V_{I(D1)} 2 V/div T V_{O(OUT)} 2 V/div t - Time - 1 ms/div



Output Switchover Response Test Circuit

Figure 2.





Output Turn-On Response Test Circuit

Figure 3.

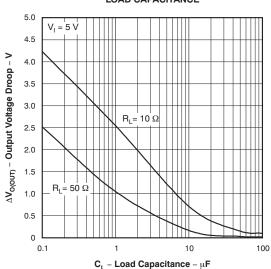


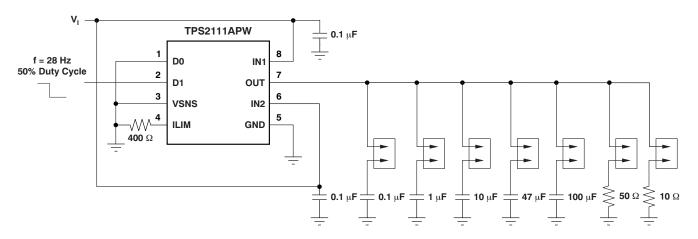
OUTPUT SWITCHOVER VOLTAGE DROOP 5 V TPS2111APW V_{I(D0)} 2 V/div 8 f = 580 Hz IN1 D0 90% Duty Cycle 2 D1 OUT V_{I(D1)} 2 V/div VSNS IN2 $C_L = 1 \mu F$ \geq 50 Ω GND $\mathbf{400}~\Omega$ V_{O(OUT)} 2 V/div 🟪 0.1 μF $C_L = 0 \,\mu \dot{F}$ **Output Switchover Voltage Droop Test Circuit** t - Time - 40 μs/div

Figure 4.



OUTPUT SWITCHOVER VOLTAGE DROOP vs LOAD CAPACITANCE

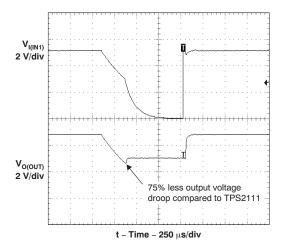


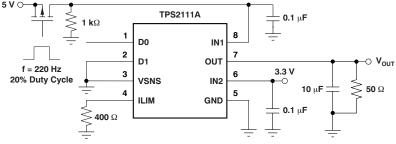


Output Switchover Voltage Droop Test Circuit Figure 5.



AUTO SWITCHOVER VOLTAGE DROOP

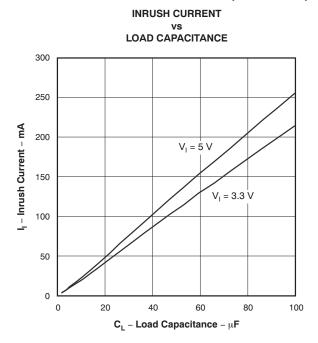


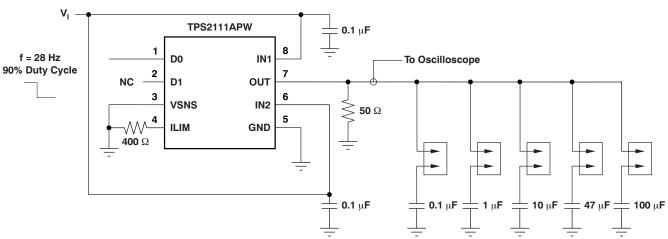


Auto Switchover Voltage Droop Test Circuit

Figure 6.

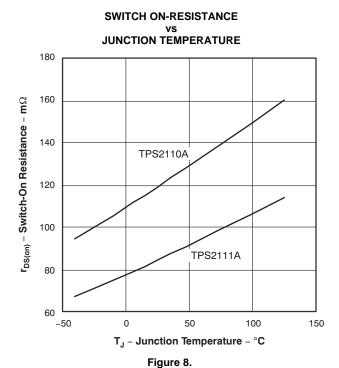




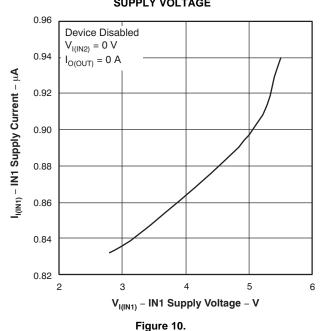


Output Capacitor Inrush Current Test Circuit Figure 7.

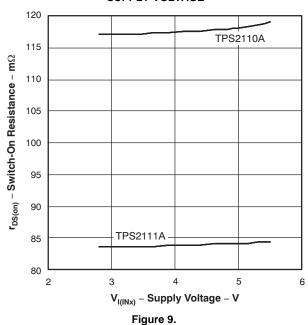




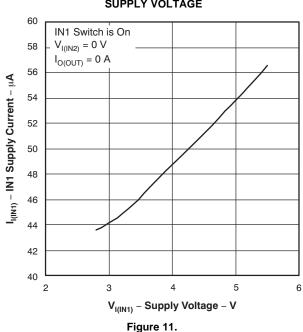
IN1 SUPPLY CURRENT VS SUPPLY VOLTAGE



SWITCH ON-RESISTANCE vs SUPPLY VOLTAGE



IN1 SUPPLY CURRENT vs SUPPLY VOLTAGE



SUPPLY CURRENT

vs JUNCTION TEMPERATURE

 $I_{I(IN1)}$

 $I_{I(IN2)}$

100

150



TYPICAL CHARACTERISTICS (continued)

80

70

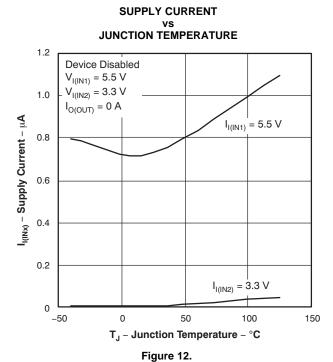
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IN1 Switch is On

 $V_{I(IN1)} = 5.5 \text{ V}$

 $V_{I(IN2)} = 3.3 \text{ V}$

 $I_{O(OUT)} = 0 A$



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Figure 13.

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 T_J – Junction Temperature – $^{\circ}$ C



APPLICATION INFORMATION

Some applications have two energy sources, one of which should be used in preference to another. Figure 14 shows a circuit that will connect IN1 to OUT until the voltage at IN1 falls below a user-specified value. Once the voltage on IN1 falls below this value, the TPS211xA will select the higher of the two supplies. This usually means that the TPS211xA will swap to IN2.

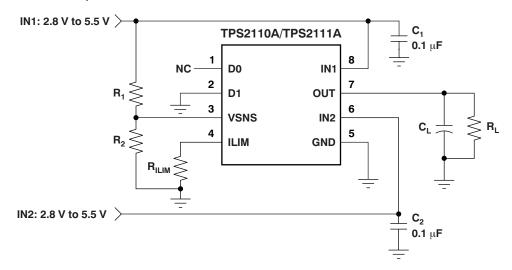


Figure 14. Auto-Selecting for a Dual Power-Supply Application

In Figure 15, the multiplexer selects between two power supplies based upon the EN1 logic signal. OUT connects to IN1 if EN1 is logic '1'; otherwise, OUT connects to IN2. The logic thresholds for the D1 terminal are compatible with both TTL and CMOS logic.

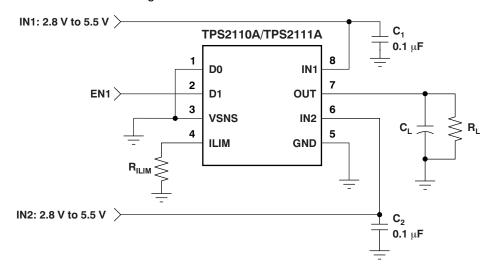


Figure 15. Manually Switching Power Sources

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DETAILED DESCRIPTION

AUTO-SWITCHING MODE

D0 equal to logic '1' and D1 equal to logic '0' selects the auto-switching mode. In this mode, OUT connects to IN1 if $V_{I(VSNS)}$ is greater than 0.8 V; otherwise, OUT connects to the higher of IN1 and IN2.

The VSNS terminal includes hysteresis equal to 3.75% to 7.5% of the threshold selected for transition from the primary supply to the higher of the two supplies. This hysteresis helps avoid repeated switching from one supply to the other due to resistive drops.

MANUAL SWITCHING MODE

D0 equal to logic '0' selects the manual-switching mode. In this mode, OUT connects to IN1 if D1 is equal to logic '1'; otherwise, OUT connects to IN2.

N-CHANNEL MOSFETs

Two internal high-side power MOSFETs implement a single-pole double-throw (SPDT) switch. Digital logic selects the IN1 switch, IN2 switch, or no switch (Hi-Z state). The MOSFETs have no parallel diodes so output-to-input current cannot flow when the FET is off. An integrated comparator prevents turn-on of a FET switch if the output voltage is greater than the input voltage.

CROSS-CONDUCTION BLOCKING

The switching circuitry ensures that both power switches will never conduct at the same time. A comparator monitors the gate-to-source voltage of each power FET and allows a FET to turn on only if the gate-to-source voltage of the other FET is below the turn-on threshold voltage.

REVERSE-CONDUCTION BLOCKING

When the TPS211xA switches from a higher-voltage supply to a lower-voltage supply, current can potentially flow back from the load capacitor into the lower-voltage supply. To minimize such reverse conduction, the TPS211xA will not connect a supply to the output until the output voltage has fallen to within 100 mV of the supply voltage. Once a supply has been connected to the output, it will remain connected regardless of output voltage.

CHARGE PUMP

The higher of supplies IN1 and IN2 powers the internal charge pump. The charge pump provides power to the current limit amplifier and allows the output FET gate voltage to be higher than the IN1 and IN2 supply voltages. A gate voltage that is higher than the source voltage is necessary to turn on the N-channel FET.

CURRENT LIMITING

A resistor R_{ILIM} from ILIM to GND sets the current limit to $250/R_{ILIM}$ and $500/R_{ILIM}$ for the TPS2110A and TPS2111A, respectively. Setting resistor R_{ILIM} equal to zero is not recommended as that disables current limiting.

OUTPUT VOLTAGE SLEW-RATE CONTROL

The TPS211xA slews the output voltage at a slow rate when OUT switches to IN1 or IN2 from the Hi-Z state (see the Truth Table). A slow slew rate limits the inrush current into the load capacitor. High inrush currents can glitch the voltage bus and cause a system to hang up or reset. It can also cause reliability issues—like pit the connector power contacts, when hot-plugging a load such as a PCI card. The TPS211xA slews the output voltage at a much faster rate when OUT switches between IN1 and IN2. The fast rate minimizes the output voltage droop and reduces the output voltage hold-up capacitance requirement.

Submit Documentation Feedback



REVISION HISTORY

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

C	nanges from Original (March, 2004) to Revision A	Page
•	Updated document to current format	1
•	Deleted package information from Available Options table	2
•	Revised Ordering Information table	2
•	Deleted lead temperature and storage temperature specifications from, added electrostatic discharge specifications to Absolute Maximum Ratings table; changed operating virtual junction temperature specification; deleted ESD Protection table	
•	Updated conditions for Electrical Characteristics	3
•	Deleted footnote 1 for Electrical Characteristics table	3
•	Deleted footnote 1 for Switching Characteristics table	5

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TPS2110APW	ACTIVE	TSSOP	PW	8	150	RoHS & Green	(6) NIPDAU	Level-1-260C-UNLIM	-40 to 85	2110A	Samples
TPS2110APWR	ACTIVE	TSSOP	PW	8	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	2110A	Samples
TPS2111APW	ACTIVE	TSSOP	PW	8	150	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	2111A	Samples
TPS2111APWR	ACTIVE	TSSOP	PW	8	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	2111A	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

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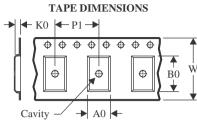
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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





	•
A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS2110APWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
TPS2111APWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1

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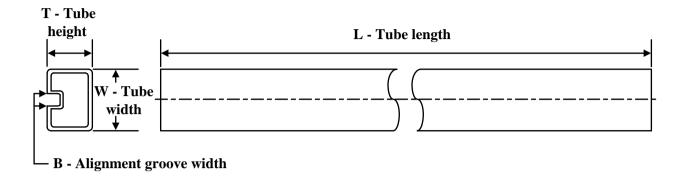
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins SPQ		Length (mm)	Width (mm)	Height (mm)	
TPS2110APWR	TSSOP	PW	8	2000	356.0	356.0	35.0	
TPS2111APWR	TSSOP	PW	8	2000	356.0	356.0	35.0	

PACKAGE MATERIALS INFORMATION

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TUBE

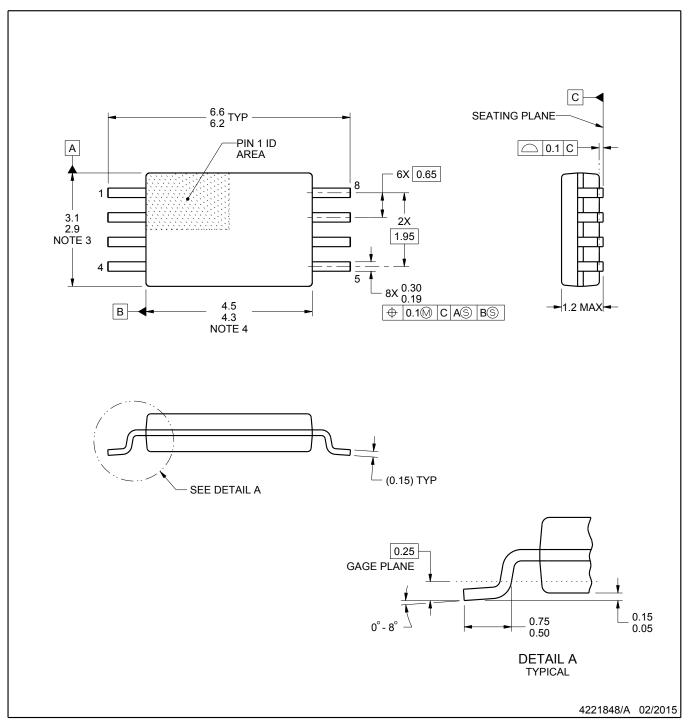


*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
TPS2110APW	PW	TSSOP	8	150	530	10.2	3600	3.5
TPS2111APW	PW	TSSOP	8	150	530	10.2	3600	3.5



SMALL OUTLINE PACKAGE



NOTES:

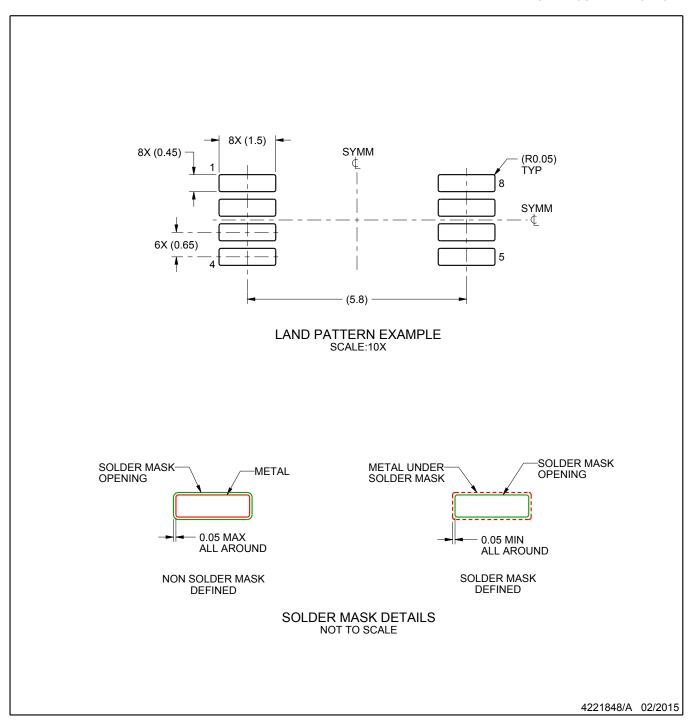
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153, variation AA.



SMALL OUTLINE PACKAGE



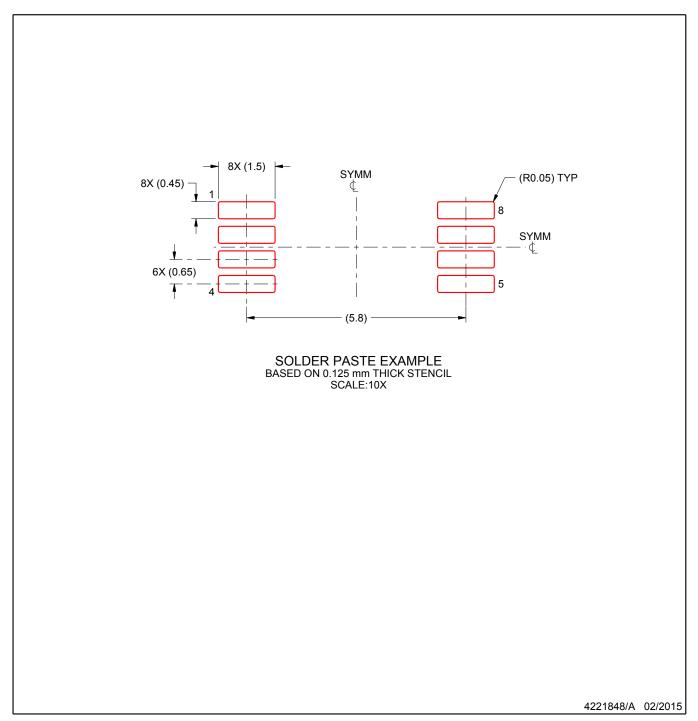
NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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